

IRF7311TRPBF-VB Datasheet

Dual N-Channel 20-V (D-S) MOSFET

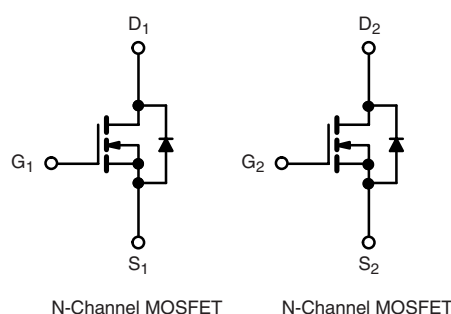
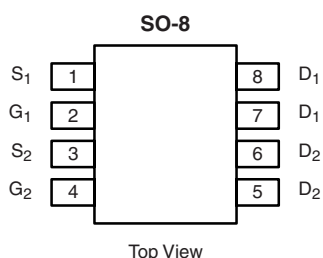
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
20	0.019 at $V_{GS} = 4.5$ V	7.1
	0.026 at $V_{GS} = 2.5$ V	6.0

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available



ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current ($T_J = 150$ °C) ^a	$T_A = 25$ °C	I_D	7.1	A
	$T_A = 70$ °C		5.7	
Pulsed Drain Current (10 μ s Pulse Width)		I_{DM}	40	
Continuous Source Current (Diode Conduction) ^a		I_S	1.7	W
Maximum Power Dissipation ^a	$T_A = 25$ °C	P_D	2	
	$T_A = 70$ °C		1.3	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	62.5	°C/W

Notes:

a. Surface Mounted on FR4 board, $t \leq 10$ s.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	0.6		1.5	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 12\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 20\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^{\circ}\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 4.5\text{ V}$	20			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}$, $I_D = 7.1\text{ A}$		0.019		Ω
		$V_{GS} = 2.5\text{ V}$, $I_D = 6.0\text{ A}$		0.026		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}$, $I_D = 7.1\text{ A}$		27		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 1.7\text{ A}$, $V_{GS} = 0\text{ V}$			1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 10\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 7.1\text{ A}$		9.5		nC
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}			2.5		
Gate Resistance	R_g	$f = 1\text{ MHz}$		1.6	2.7	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}$, $R_L = 10\text{ }\Omega$ $I_D \cong 1\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 10\text{ }\Omega$		10		ns
Rise Time	t_r			15		
Turn-Off Delay Time	$t_{d(off)}$			38		
Fall Time	t_f			25		
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.7\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$		26		

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Output Characteristics



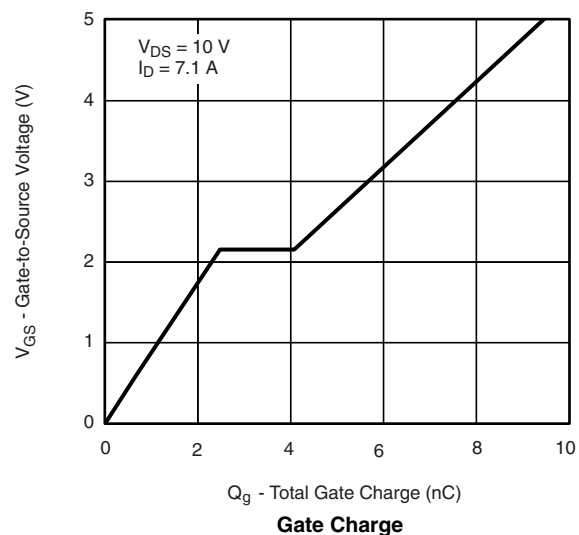
Transfer Characteristics



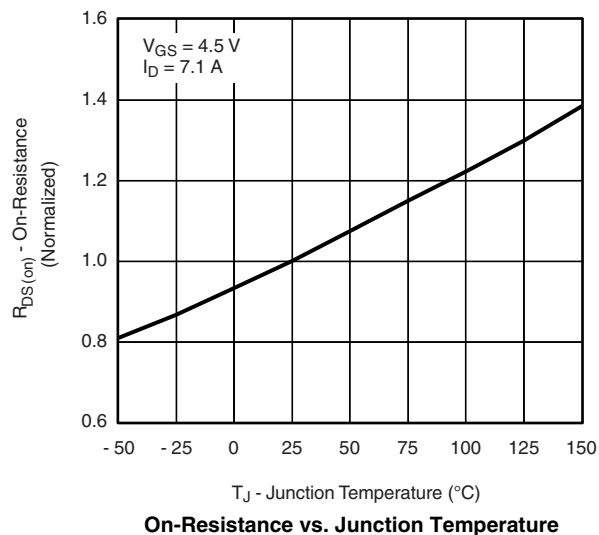
On-Resistance vs. Drain Current



Capacitance



Gate Charge

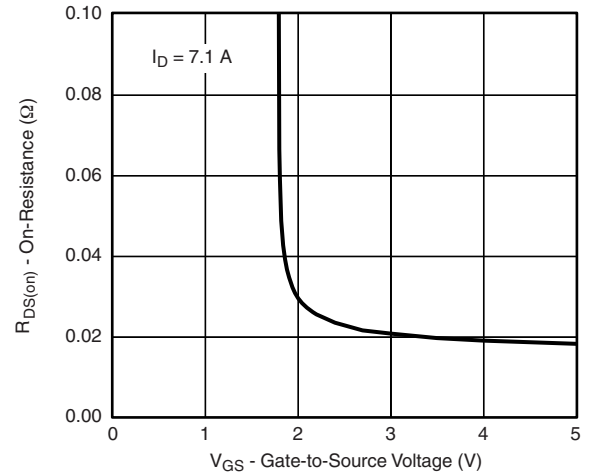


On-Resistance vs. Junction Temperature

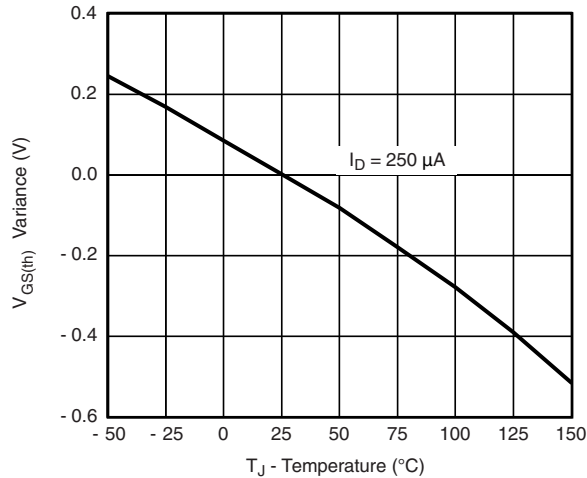
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



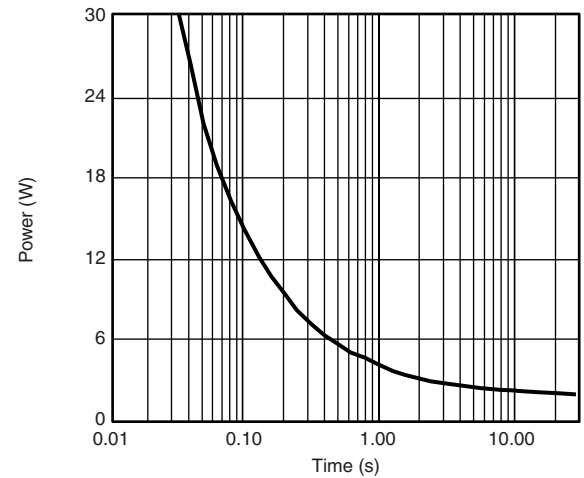
Source-Drain Diode Forward Voltage



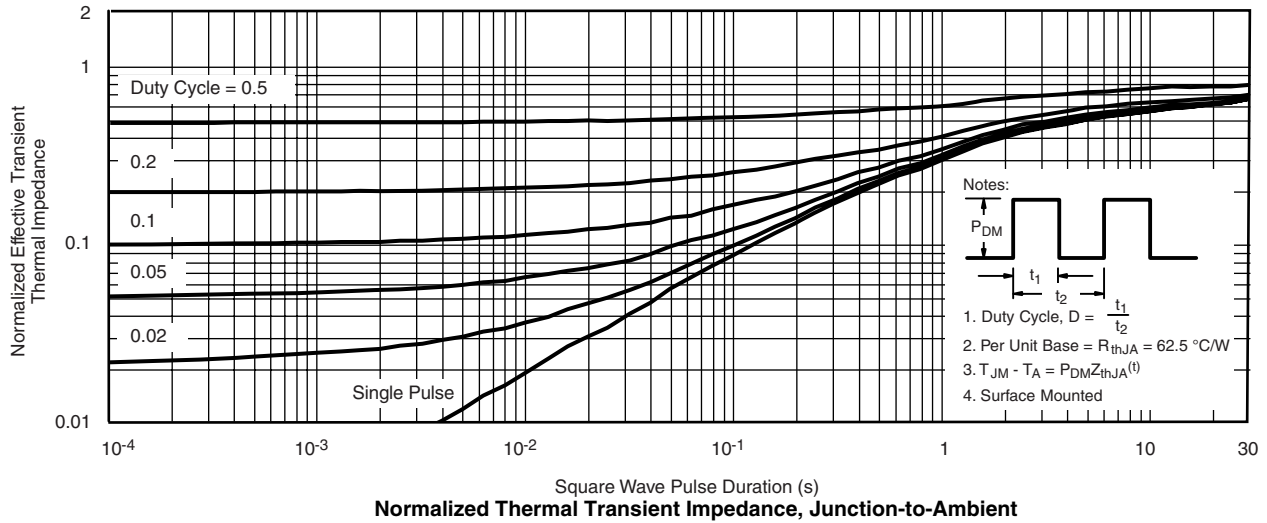
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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